

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

ECH8419 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)1=13m Ω (typ.)
- · 4V drive
- · Halogen free compliance
- · Protection diode in

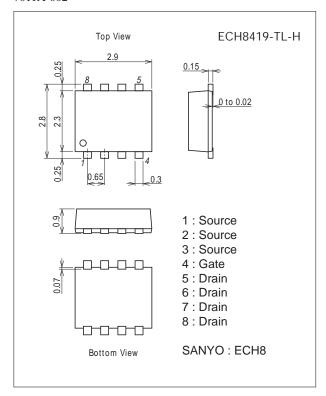
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		35	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	ID		9	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	40	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7011A-002



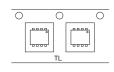
Product & Package Information

• Package : ECH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

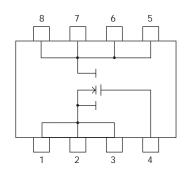
Packing Type : TL



Marking



Electrical Connection

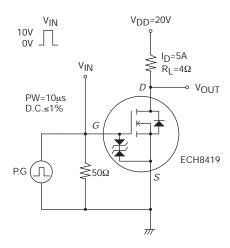


ECH8419

Electrical Characteristics at Ta=25°C

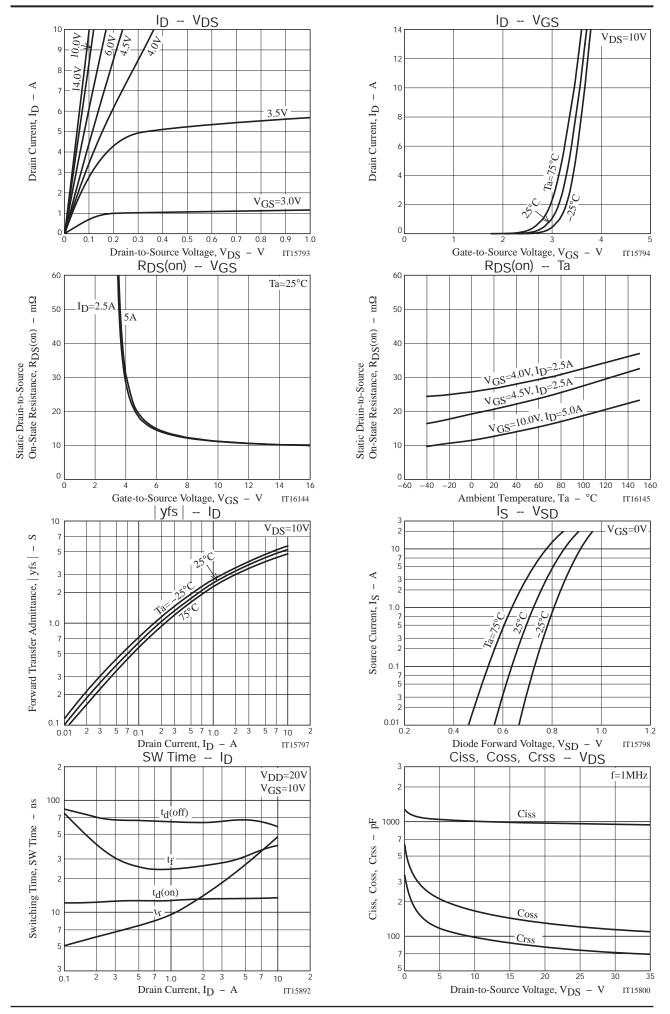
Parameter	Cymhal	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =35V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =5A		4.3		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =5A, V _{GS} =10V		13	17	mΩ	
	R _{DS} (on)2	I _D =2.5A, V _{GS} =4.5V		21	30	mΩ	
	R _{DS} (on)3	I _D =2.5A, V _{GS} =4V		27	38	mΩ	
Input Capacitance	Ciss			960		pF	
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		130		pF	
Reverse Transfer Capacitance	Crss			80		pF	
Turn-ON Delay Time	t _d (on)			13		ns	
Rise Time	t _r	Can appointed Toot Circuit		26		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		66		ns	
Fall Time	tf			31		ns	
Total Gate Charge	Qg			19		nC	
Gate-to-Source Charge	Qgs	V _{DS} =20V, V _{GS} =10V, I _D =9A		3.9		nC	
Gate-to-Drain "Miller" Charge	Qgd			3.8		nC	
Diode Forward Voltage	V _{SD}	IS=9A, VGS=0V		0.85	1.2	V	

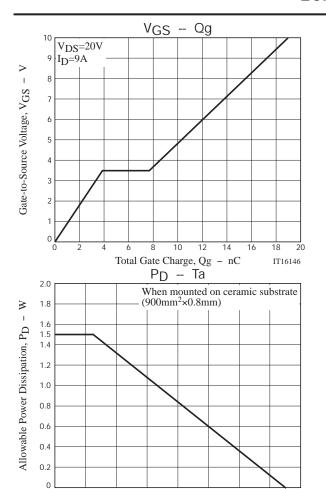
Switching Time Test Circuit



Ordering Information

Device	Device Package		memo	
ECH8419-TL-H	CH8419-TL-H ECH8		Pb Free and Halogen Free	





80

Ambient Temperature, Ta - °C

100

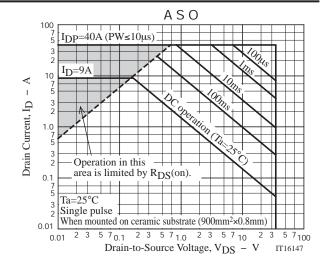
140

160

IT16148

20

0

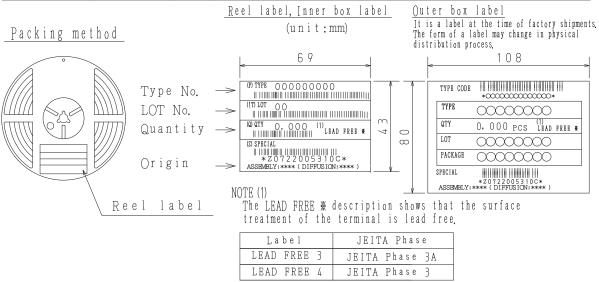


Embossed Taping Specification

ECH8419-TL-H

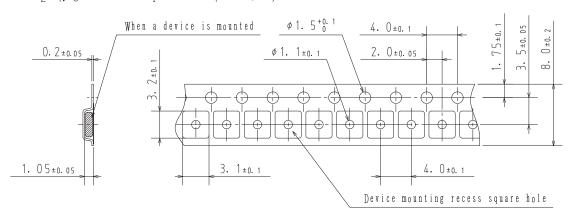
1. Packing Format

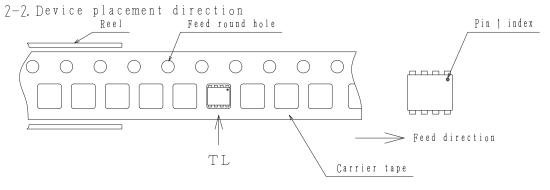
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	format
	Туре	Reel	Inner box	Outer box	Inner $BOX(C-1)$	Outer BOX (A-7)
ECH8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained
					Dimensions:mm (external)	Dimensions:mm (external)
					183×72×185	440×195×210



2. Taping configuration

2-1. Carrier tape size (unit:mm)

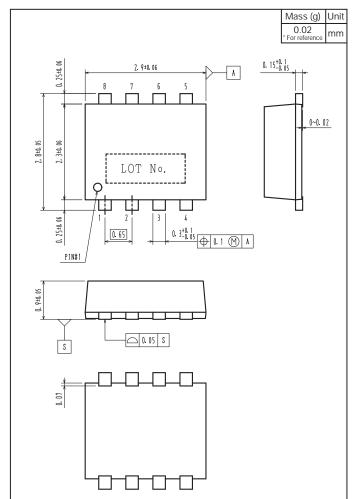




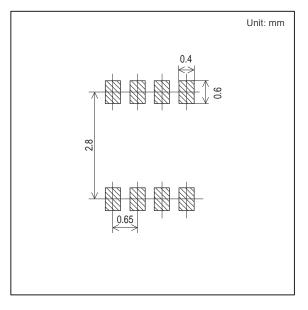
Those with pin 1 index on the feed hole side · · · · · TL

Outline Drawing

ECH8419-TL-H



Land Pattern Example



Note on usage: Since the ECH8419 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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